

Title (en)

Method of detection of damages on integrated circuit devices

Title (de)

Verfahren zur Erkennung von Beschädigungen an IC-Bauelementen

Title (fr)

Méthode de la reconnaissance de l'endommagement sur des dispositifs à circuits intégrés

Publication

EP 1335423 A3 20080813 (DE)

Application

EP 03002386 A 20030204

Priority

DE 10205517 A 20020208

Abstract (en)

[origin: EP1335423A2] The method involves measuring sound emissions during separation of integrated circuit components from a wafer foil, comparing the emissions with normalized stored sound emission curves and removing a component from the processing process if the measured emissions are outside a tolerance range about the normalized stored curves.

IPC 8 full level

H01L 21/66 (2006.01)

CPC (source: EP)

H01L 22/12 (2013.01); **H01L 2924/0002** (2013.01)

Citation (search report)

- [A] JP H11221760 A 19990817 - NIPPEI TOYAMA CORP
- [A] WO 0047953 A1 20000817 - SIGNALYSIS L L C [US]
- [A] JP 2001110758 A 20010420 - MATSUSHITA ELECTRONICS CORP
- [A] US 4419562 A 19831206 - JON MIN-CHUNG [US], et al
- [X] 19000101, 1 January 1900 (1900-01-01), XP008093529
- [DA] VON RABEN K U: "Controlling relevant bonding parameters of modern bonders", 19880509; 19880509 - 19880511, 9 May 1988 (1988-05-09), pages 558 - 563, XP010077270

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IT LI LU MC NL PT SE SI SK TR

Designated extension state (EPC)

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